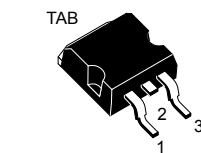
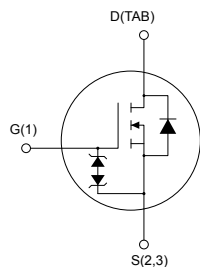


## Automotive-grade N-channel 600 V, 70 mΩ typ., 36 A MDmesh™ DM6 Power MOSFET in an H<sup>2</sup>PAK-2 package


 H<sup>2</sup>PAK-2


NCHG10TAB523TZ



### Product status link


[STH47N60DM6-2AG](#)

### Product summary

<b>Order code</b>	STH47N60DM6-2AG
<b>Marking</b>	47N60DM6
<b>Package</b>	H <sup>2</sup> PAK-2
<b>Packing</b>	Tape and reel

## Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STH47N60DM6-2AG	600 V	80 mΩ	36 A

- AEC-Q101 qualified 
- Fast-recovery body diode
- Lower R<sub>DS(on)</sub> per area vs previous generation
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

## Applications

- Switching applications

## Description

This high-voltage N-channel Power MOSFET is part of the MDmesh™ DM6 fast-recovery diode series. Compared with the previous MDmesh fast generation, DM6 combines very low recovery charge (Q<sub>rr</sub>), recovery time (t<sub>rr</sub>) and excellent improvement in R<sub>DS(on)</sub> per area with one of the most effective switching behaviors available in the market for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	±25	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$	36	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	23	A
$I_D^{(1)}$	Drain current (pulsed)	137	A
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ °C}$	250	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	50	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	100	
$T_J$	Operating junction temperature range	-55 to 150	°C
$T_{stg}$	Storage temperature range		

1. Pulse width limited by safe operating area
2.  $I_{SD} \leq 36\text{ A}$ ,  $di/dt \leq 800\text{ A}/\mu\text{s}$ ,  $V_{DS(peak)} < V_{(BR)DSS}$ ,  $V_{DD} = 480\text{ V}$
3.  $V_{DS} \leq 480\text{ V}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.5	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	30	

1. When mounted on FR-4 board of 1 inch<sup>2</sup>, 2oz Cu.

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{Jmax}$ )	7	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$ , $I_D = I_{AR}$ , $V_{DD} = 100\text{ V}$ )	700	mJ

## 2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified

**Table 4. On/off state**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	600			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$ , $T_C = 125\text{ }^\circ\text{C}^{(1)}$			100	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$			$\pm 1$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3.25	4	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 18\text{ A}$		70	80	m $\Omega$

1. Defined by design, not subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	2350	-	pF
$C_{oss}$	Output capacitance		-	160	-	pF
$C_{riss}$	Reverse transfer capacitance		-	2	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}$ , $V_{GS} = 0\text{ V}$	-	416	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.6	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 36\text{ A}$ ,	-	55	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	12	-	nC
$Q_{gd}$	Gate-drain charge	(see Figure 14. Test circuit for gate charge behavior)	-	31	-	nC

1.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 18\text{ A}$ ,	-	23	-	ns
$t_r$	Rise time	$R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$	-	5.5	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	57	-	ns
$t_f$	Fall time		-	9	-	ns

**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		36	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		137	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 36\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 36\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$	-	115		ns
$Q_{rr}$	Reverse recovery charge		-	0.54		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	9.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 36\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	-	210		ns
$Q_{rr}$	Reverse recovery charge		-	2.1		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	20.4	

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 8. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0\text{ A}$	$\pm 30$	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

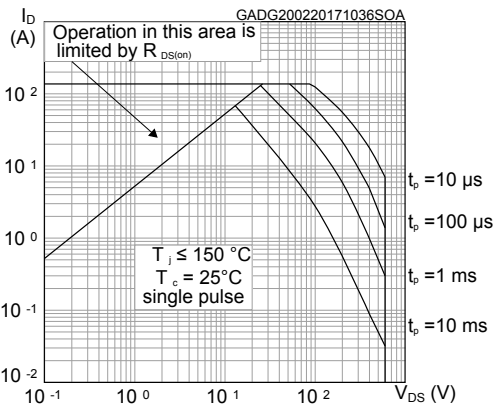


Figure 2. Thermal impedance

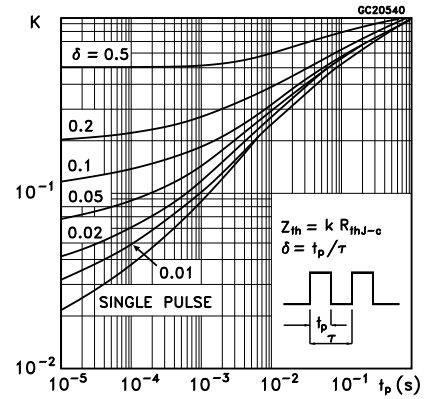


Figure 3. Output characteristics

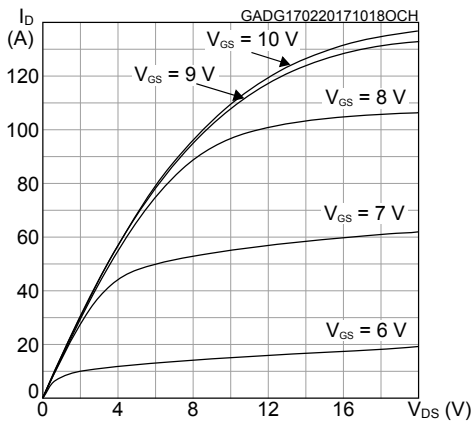


Figure 4. Transfer characteristics

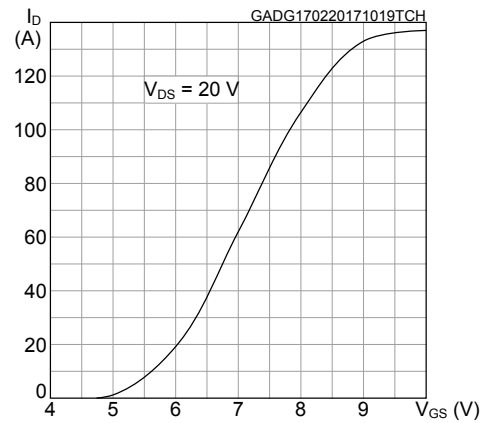


Figure 5. Gate charge vs gate-source voltage

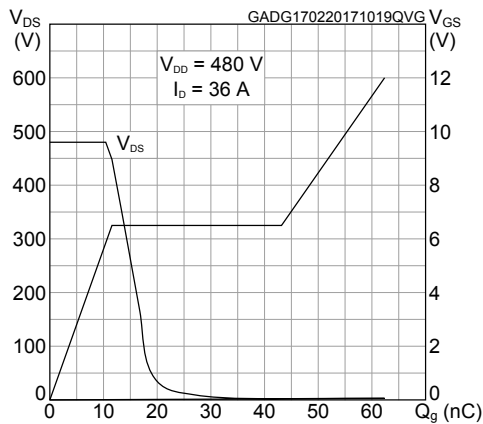


Figure 6. Static drain-source on-resistance

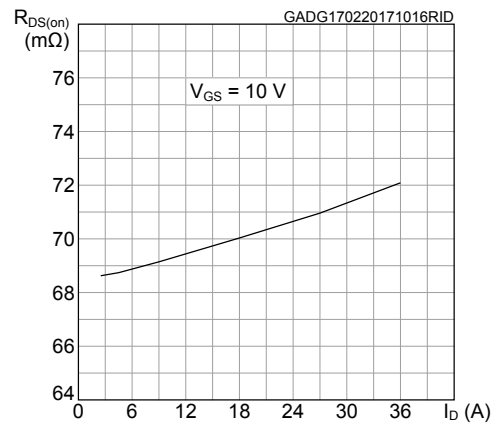


Figure 7. Capacitance variations

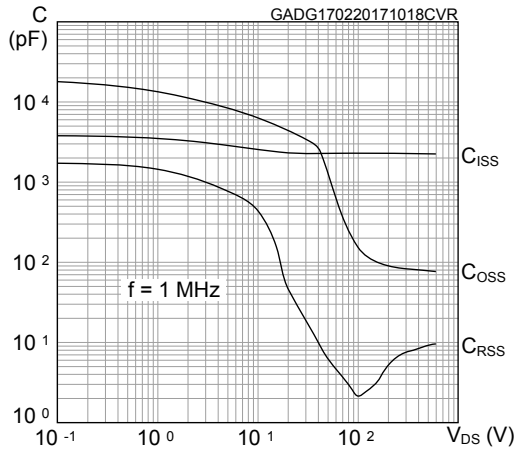


Figure 8. Normalized gate threshold voltage vs temperature

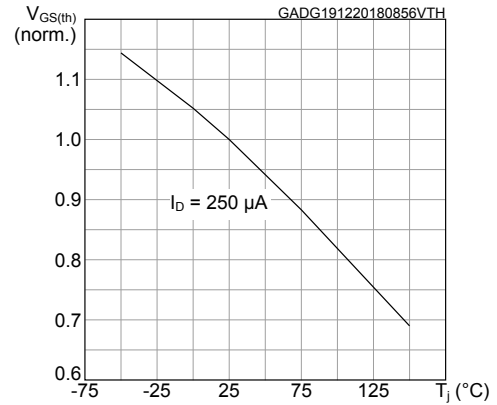


Figure 9. Normalized on-resistance vs temperature

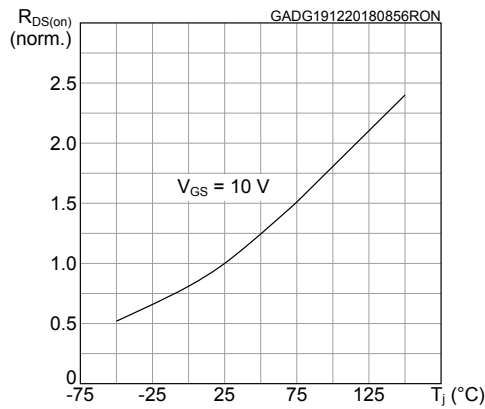


Figure 10. Normalized V<sub>(BR)DSS</sub> vs temperature

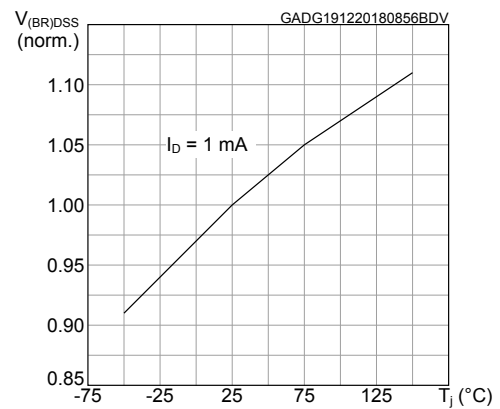


Figure 11. Source-drain diode forward characteristics

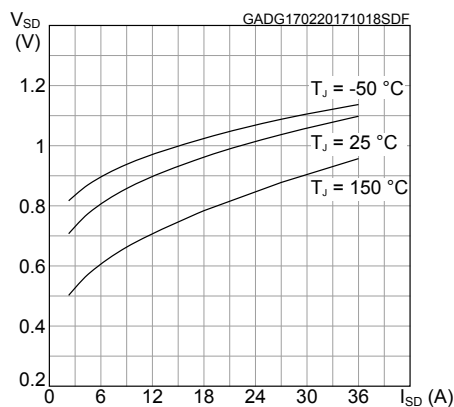
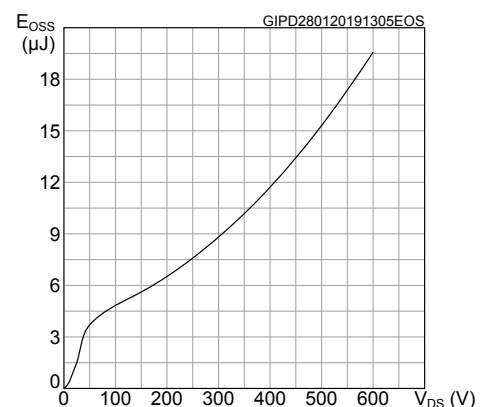


Figure 12. Output capacitance stored energy



### 3 Test circuits

**Figure 13. Test circuit for resistive load switching times**


AM01468v1

**Figure 14. Test circuit for gate charge behavior**


AM01469v1

**Figure 15. Test circuit for inductive load switching and diode recovery times**


AM01470v1

**Figure 16. Unclamped inductive load test circuit**


AM01471v1

**Figure 17. Unclamped inductive waveform**


AM01472v1

**Figure 18. Switching time waveform**


AM01473v1

## 4 Package information

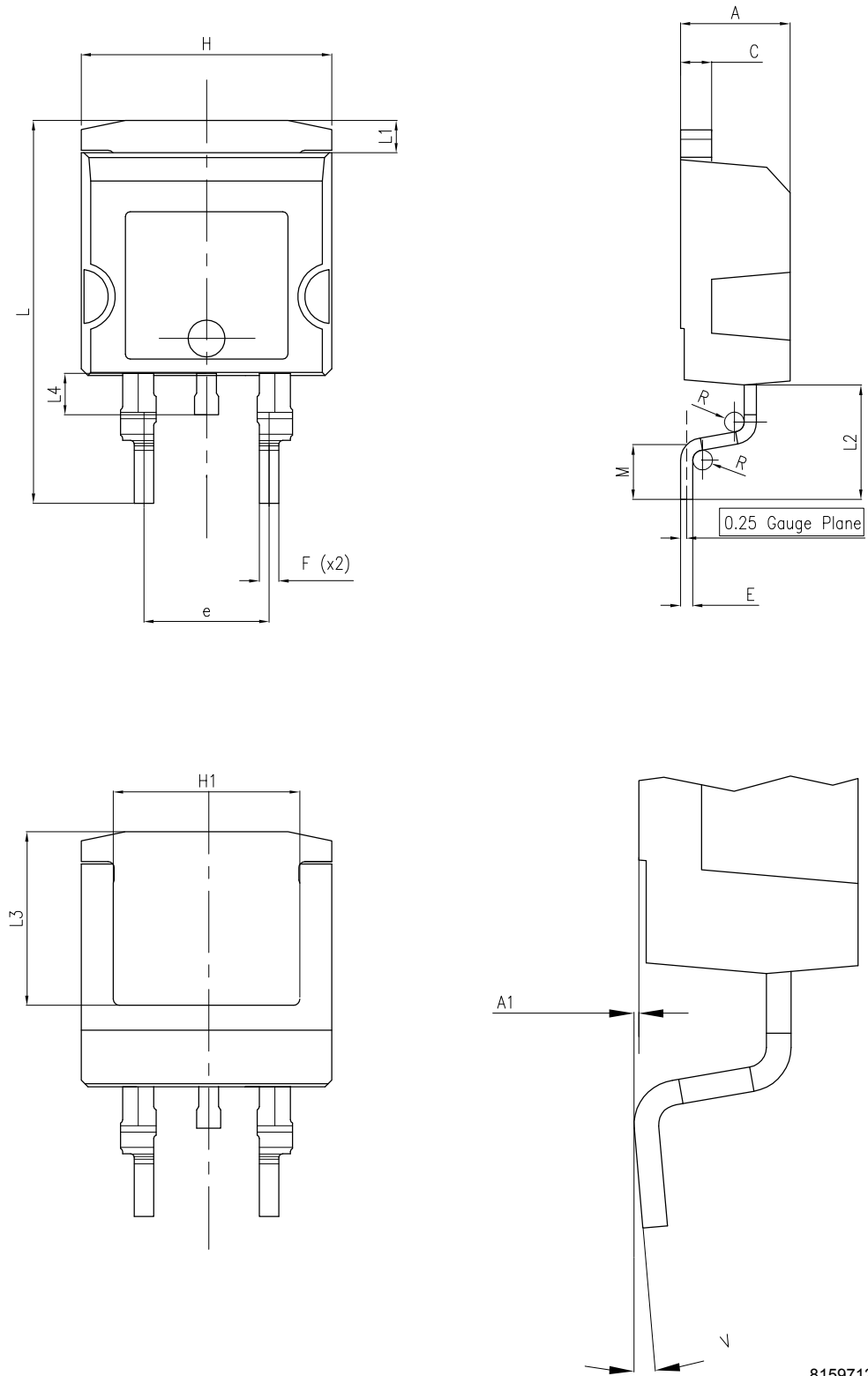
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In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.



### 4.1 H<sup>2</sup>PAK-2 package information

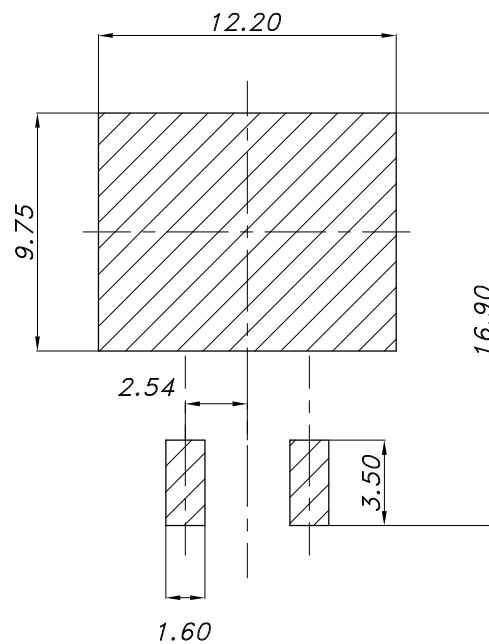
Figure 19. H<sup>2</sup>PAK-2 package outline



8159712\_8

**Table 9. H<sup>2</sup>PAK-2 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.70
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

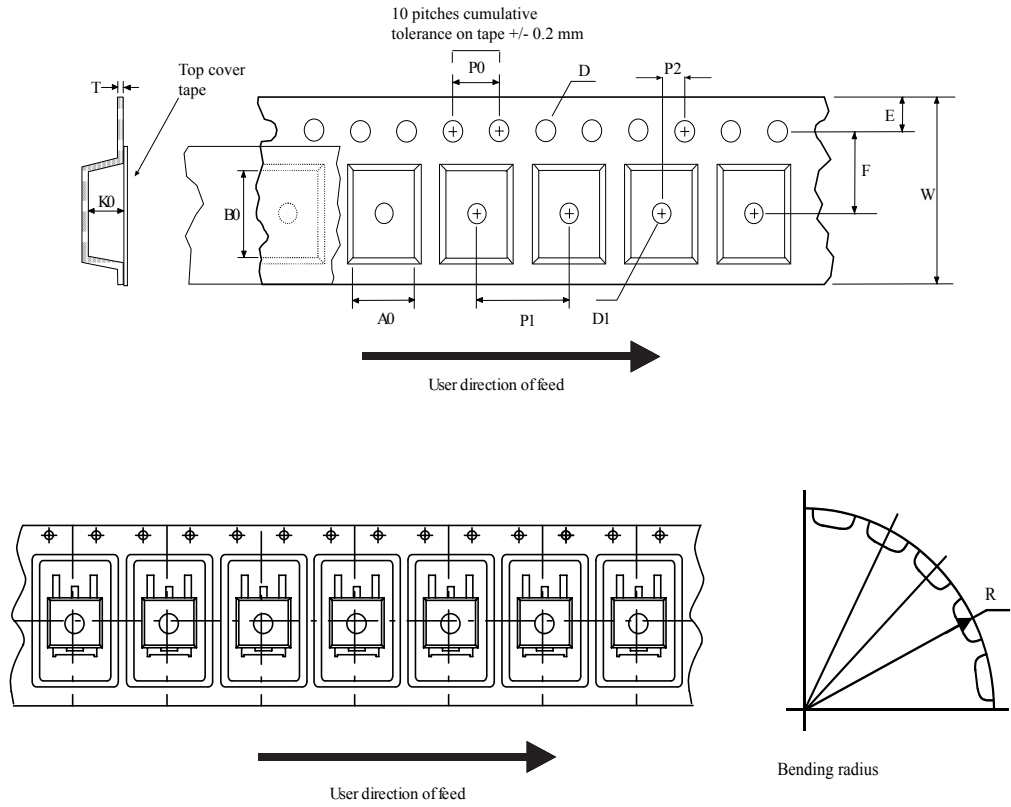
**Figure 20. H<sup>2</sup>PAK-2 recommended footprint**


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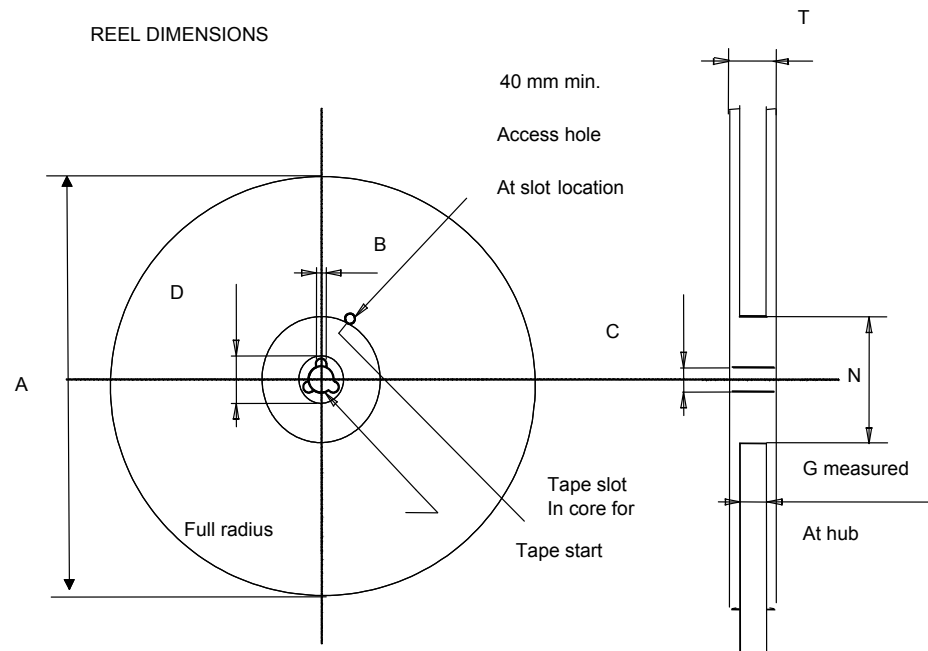
Note: Dimensions are in mm.

## 4.2 Packing information

Figure 21. Tape outline



AM08852v2

**Figure 22. Reel outline**

**Table 10. Tape and reel mechanical data**

Dim.	Tape		Dim.	Reel	
	mm			mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## Revision history

**Table 11. Document revision history**

Date	Revision	Changes
09-Aug-2017	1	Initial release.
11-Mar-2019	2	Modified title and features on cover page. Modified <a href="#">Section 1 Electrical ratings</a> , <a href="#">Section 2 Electrical characteristics</a> and <a href="#">Section 2.1 Electrical characteristics (curves)</a> . Minor text changes.

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